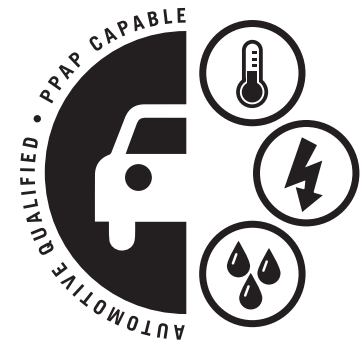


E4D20120D

Silicon Carbide Schottky Diode E-Series Automotive



Features

- 4th Generation SiC Merged PIN Schottky Technology
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- AEC-Q101 Qualified and PPAP Capable
- Humidity Resistant

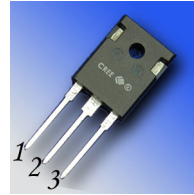
Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway
- Ideal for Outdoor Environments

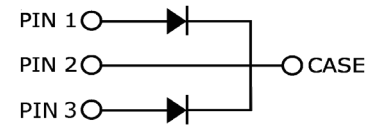
Applications

- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters
- Automotive and Traction Power Conversion
- PV Inverters

Package



TO-247-3



Part Number	Package	Marking
E4D20120D	TO-247-3	E4D20120

Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_R	DC Peak Reverse Voltage	1200	V		
I_F	Continuous Forward Current	33/66 16/32 10/20	A	$T_c=25^\circ\text{C}$ $T_c=100^\circ\text{C}$ $T_c=155^\circ\text{C}$	Fig. 3
P_{tot}	Power Dissipation	176 76	W	$T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$	Fig. 4
I_{FRM}	Repetitive Peak Forward Surge Current	45* 26*	A	$T_c=25^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse $T_c=110^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse	
dV/dt	Diode dV/dt ruggedness	250	V/ns	$V_R=0-960\text{V}$	
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		

* Per Leg, ** Per Device

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 2.2	1.8	V	$I_F = 10\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 10\text{ A}$ $T_J = 175^\circ\text{C}$	Fig. 1
I_R	Reverse Current	30 55	200	μA	$V_R = 1200\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 1200\text{ V}$ $T_J = 175^\circ\text{C}$	Fig. 2
Q_C	Total Capacitive Charge	50		nC	$V_R = 800\text{ V}$, $I_F = 10\text{ A}$ $T_J = 25^\circ\text{C}$	Fig. 5
C	Total Capacitance	712 44 32		pF	$V_R = 0\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 400\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 800\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$	Fig. 6
E_C	Capacitance Stored Energy	14		μJ	$V_R = 800\text{ V}$	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.85* 0.43**	$^\circ\text{C/W}$	Fig. 8

* Per Leg, ** Per Device

Typical Performance

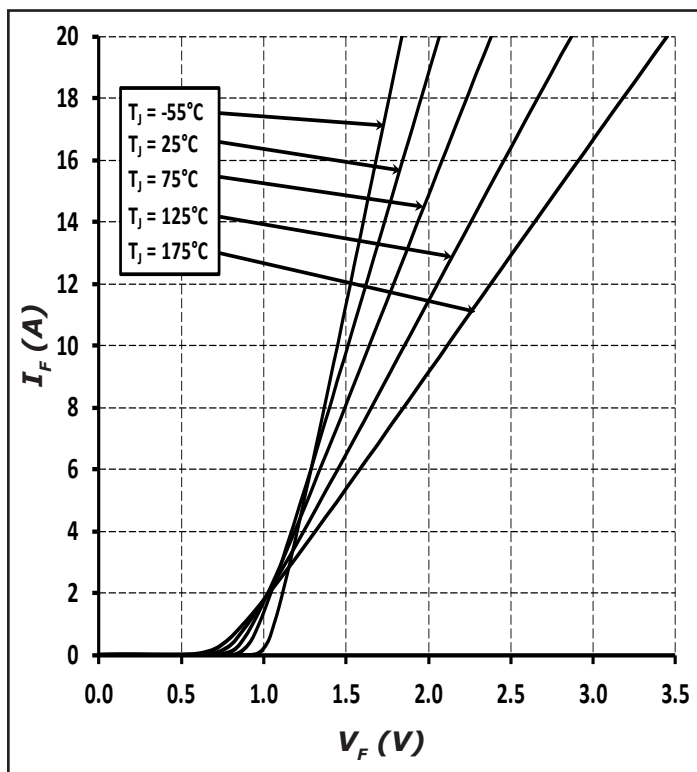


Figure 1. Forward Characteristics

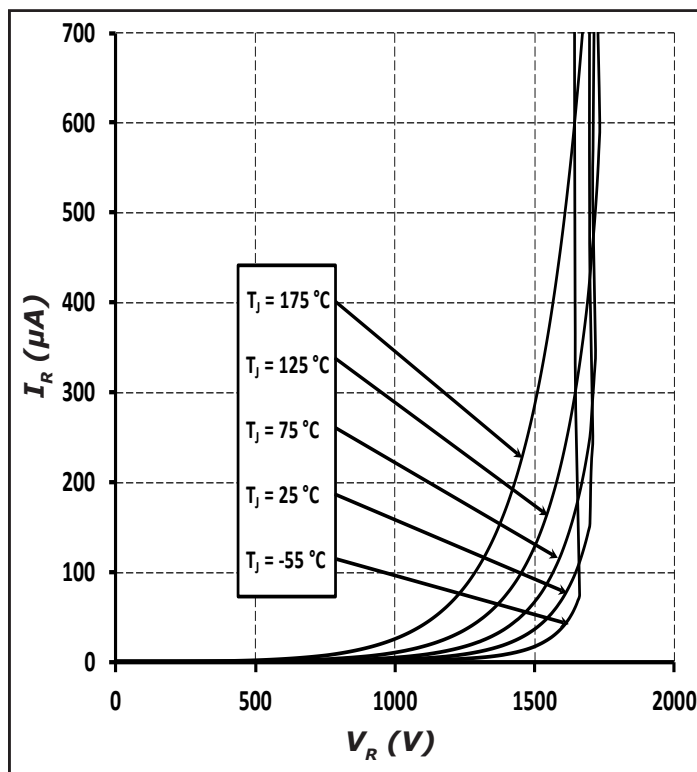


Figure 2. Reverse Characteristics

Typical Performance

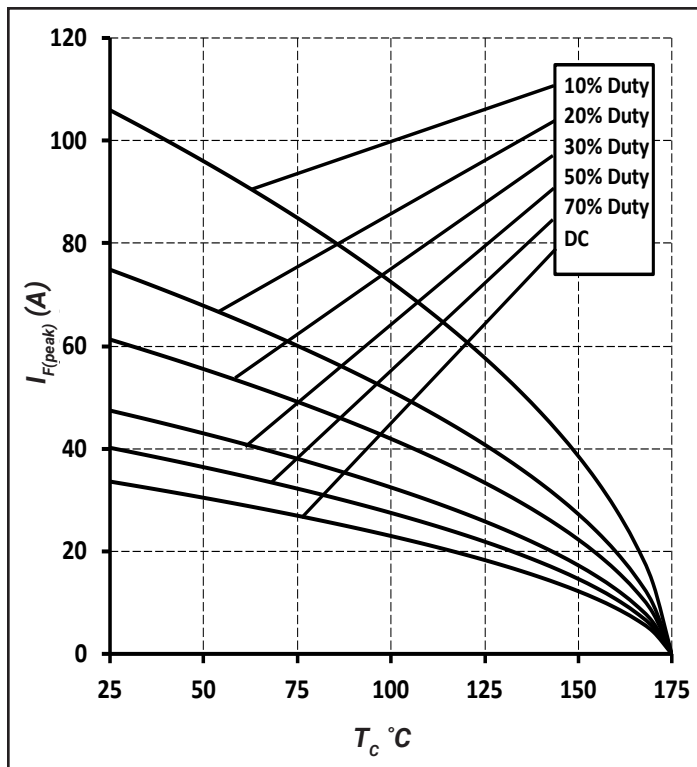


Figure 3. Current Derating

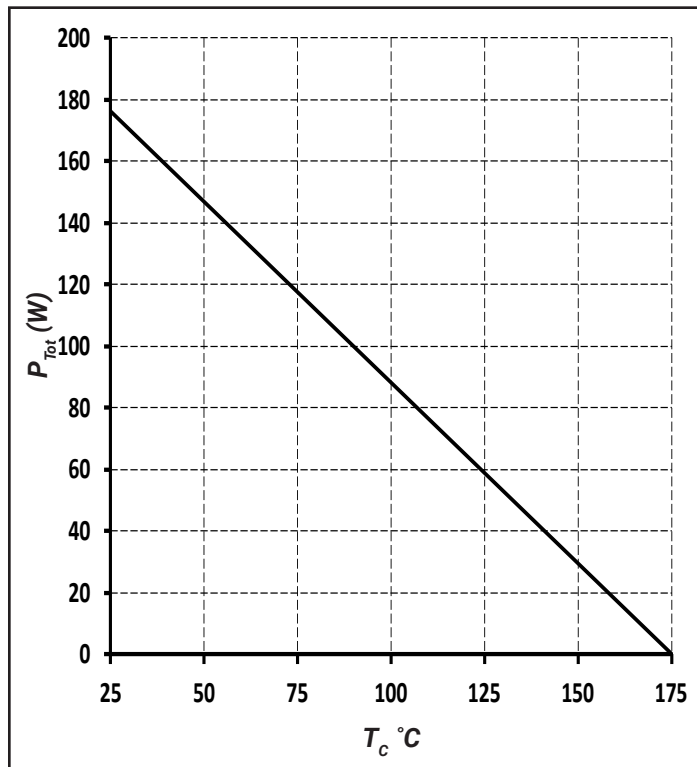


Figure 4. Power Derating

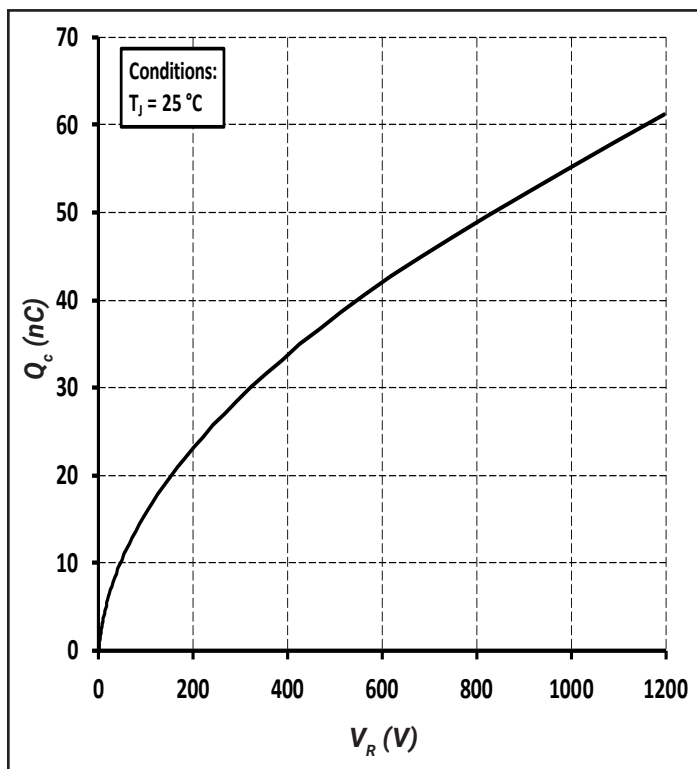


Figure 5. Recovery Charge vs. Reverse Voltage

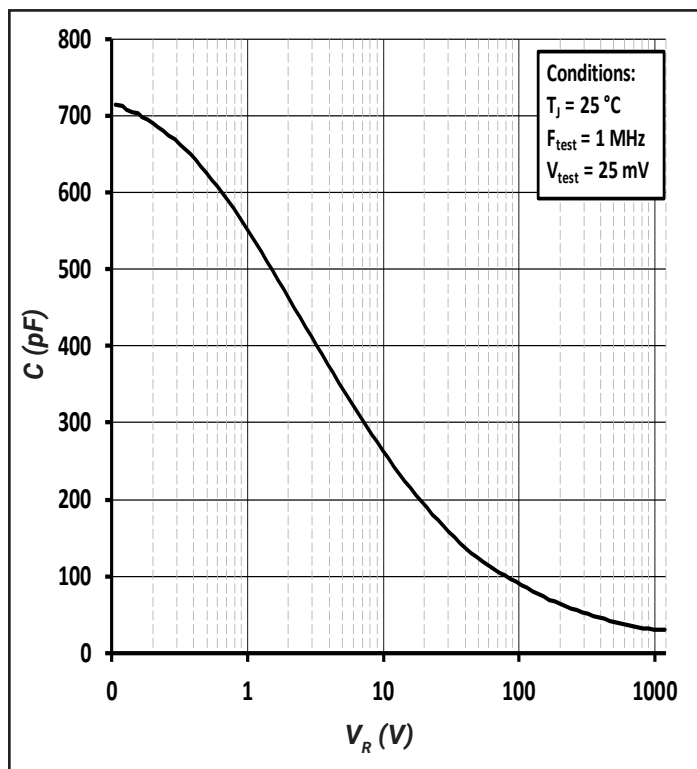


Figure 6. Capacitance vs. Reverse Voltage

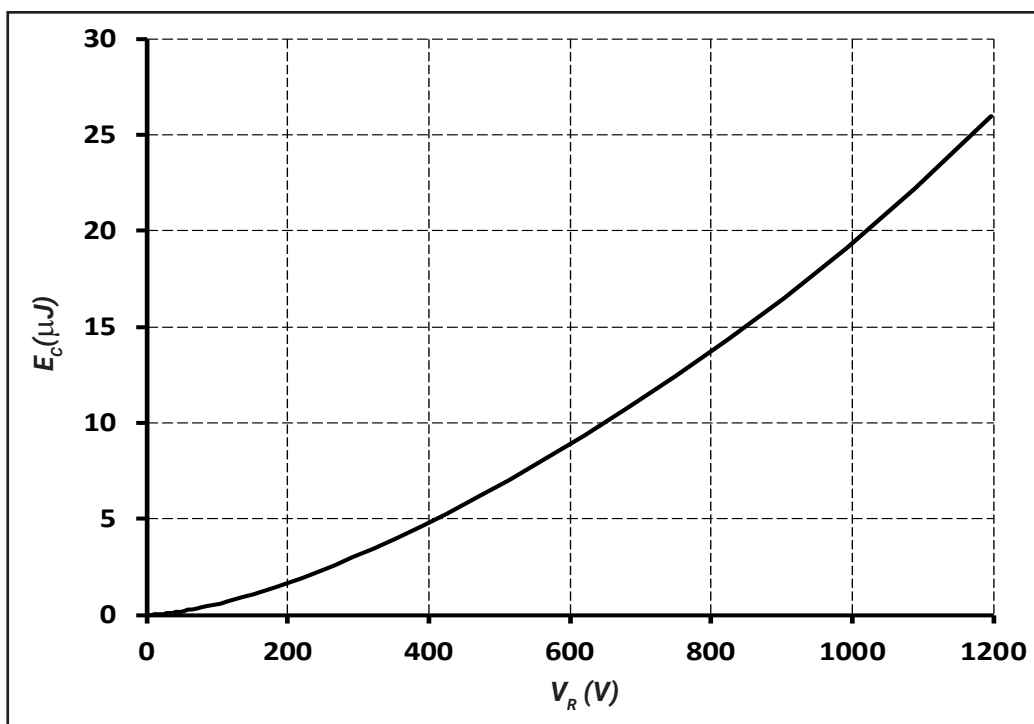


Figure 7. Typical Capacitance Stored Energy

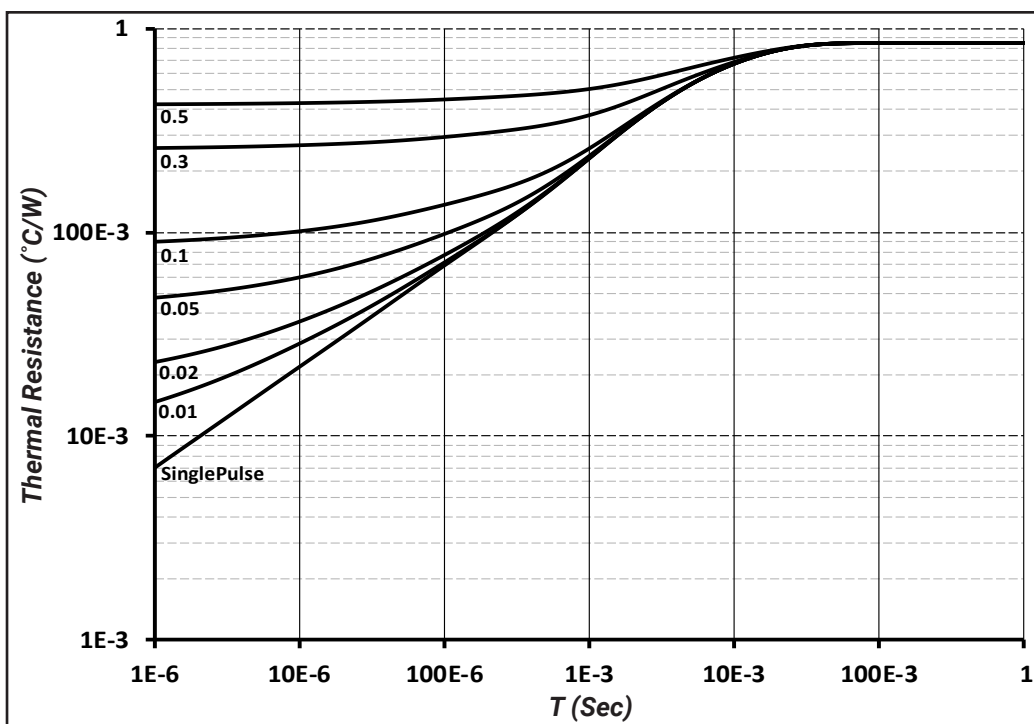
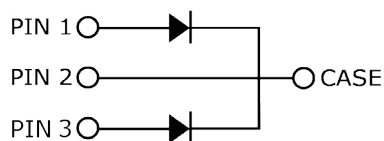
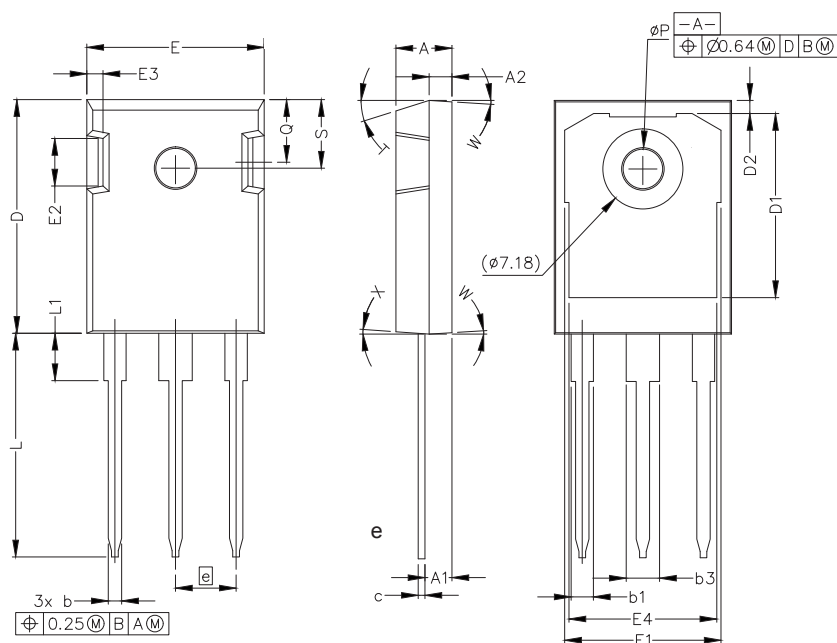


Figure 8. Transient Thermal Impedance

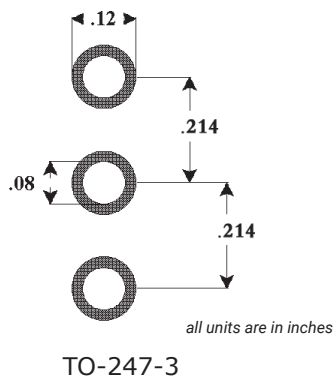
Package Dimensions

Package TO-247-3



POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.042	.052	1.07	1.33
b1	.075	.095	1.91	2.41
b3	.113	.133	2.87	3.38
c	.022	.027	0.55	0.68
D	.819	.831	20.80	21.10
D1	.640	.695	16.25	17.65
D2	.037	.049	0.95	1.25
E	.620	.635	15.75	16.13
E1	.516	.557	13.10	14.15
E2	.145	.201	3.68	5.10
E3	.039	.075	1.00	1.90
E4	.487	.529	12.38	13.43
e	.214 BSC		5.44 BSC	
L	.780	.800	19.81	20.32
L1	.161	.173	4.10	4.40
N	3			
ØP	.138	.144	3.51	3.65
Q	.216	.236	5.49	6.00
S	.238	.248	6.04	6.30
T	17.5° REF			
W	3.5° REF			
X	4° REF			

Recommended Solder Pad Layout



Part Number	Package	Marking
E4D20120D	TO-247-3	E4D20120

Note: Recommended soldering profiles can be found in the applications note here:
http://www.wolfspeed.com/power_app_notes/soldering



Notes

- **RoHS Compliance**
The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Wolfspeed representative or from the Product Ecology section of our website at <http://www.wolfspeed.com/power/tools-and-support/product-ecology>.
- **REACH Compliance**
REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a Cree representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.
- This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control systems.

Related Links

- Wolfspeed E-Series Family: <http://wolfspeed.com/E-Series>
- Wolfspeed SiC Schottky diode portfolio: <http://www.wolfspeed.com/Power/Products#SiCSchottkyDiodes>
- Schottky diode Spice models: <http://www.wolfspeed.com/power/tools-and-support/DIODE-model-request2>
- SiC MOSFET and diode reference designs: <http://go.pardot.com/l/101562/2015-07-31/349i>

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